



High Efficiency Thyristor

$V_{RRM} = 1200\text{ V}$

$I_{TAV} = 5\text{ A}$

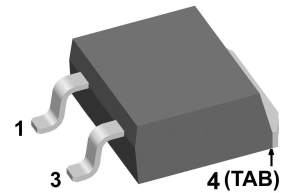
$V_T = 1.31\text{ V}$

Single Thyristor

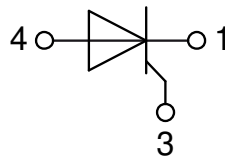
Part number

CLA5E1200PZ

Marking on Product: CLA5E1200PZ



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

Disclaimer Notice

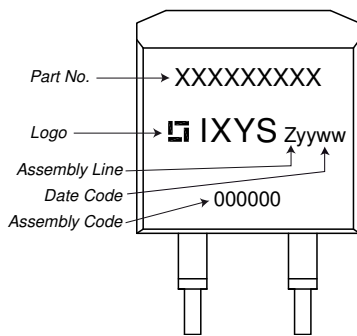
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| Thyristor | | | Ratings | | | |
|----------------|--|--|--------------------------------|------|------|------------------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| $V_{RSM/DSM}$ | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}\text{C}$ | | | 1300 | V |
| $V_{RRM/DRM}$ | max. repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}\text{C}$ | | | 1200 | V |
| I_{RD} | reverse current, drain current | $V_{R/D} = 1200\text{ V}$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 10 | μA |
| | | $V_{R/D} = 1200\text{ V}$ | $T_{VJ} = 125^{\circ}\text{C}$ | | 1 | mA |
| V_T | forward voltage drop | $I_T = 5\text{ A}$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 1.33 | V |
| | | $I_T = 10\text{ A}$ | | | 1.62 | V |
| | | $I_T = 5\text{ A}$ | $T_{VJ} = 125^{\circ}\text{C}$ | | 1.31 | V |
| | | $I_T = 10\text{ A}$ | | | 1.72 | V |
| I_{TAV} | average forward current | $T_C = 135^{\circ}\text{C}$ | $T_{VJ} = 150^{\circ}\text{C}$ | | 5 | A |
| $I_{T(RMS)}$ | RMS forward current | 180° sine | | | 7.8 | A |
| V_{T0} | threshold voltage | } for power loss calculation only | $T_{VJ} = 150^{\circ}\text{C}$ | | 0.89 | V |
| r_T | slope resistance | | | | 85 | m Ω |
| R_{thJC} | thermal resistance junction to case | | | | 1.5 | K/W |
| R_{thCH} | thermal resistance case to heatsink | | | 0.25 | | K/W |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}\text{C}$ | | 85 | W |
| I_{TSM} | max. forward surge current | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}\text{C}$ | | 70 | A |
| | | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$ | $V_R = 0\text{ V}$ | | 76 | A |
| | | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$ | $T_{VJ} = 150^{\circ}\text{C}$ | | 60 | A |
| | | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$ | $V_R = 0\text{ V}$ | | 64 | A |
| I^2t | value for fusing | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}\text{C}$ | | 25 | A ² s |
| | | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$ | $V_R = 0\text{ V}$ | | 24 | A ² s |
| | | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$ | $T_{VJ} = 150^{\circ}\text{C}$ | | 18 | A ² s |
| | | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$ | $V_R = 0\text{ V}$ | | 17 | A ² s |
| C_J | junction capacitance | $V_R = 400\text{ V}$ $f = 1\text{ MHz}$ | $T_{VJ} = 25^{\circ}\text{C}$ | 2 | | pF |
| P_{GM} | max. gate power dissipation | $t_p = 30\text{ }\mu\text{s}$ | $T_C = 150^{\circ}\text{C}$ | | 5 | W |
| | | $t_p = \text{ }\mu\text{s}$ | | | 2.5 | W |
| P_{GAV} | average gate power dissipation | | | | 0.25 | W |
| $(di/dt)_{cr}$ | critical rate of rise of current | $T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 10\text{ A}$ | | | 150 | A/ μs |
| | | $t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.1\text{ A}/\mu\text{s};$ $I_G = 0.1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 5\text{ A}$ | | | 500 | A/ μs |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage | $V = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 150^{\circ}\text{C}$ | | 500 | V/ μs |
| | | $R_{GK} = \infty$; method 1 (linear voltage rise) | | | | |
| V_{GT} | gate trigger voltage | $V_D = 6\text{ V}$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 1.8 | V |
| | | | $T_{VJ} = -40^{\circ}\text{C}$ | | 1.9 | V |
| I_{GT} | gate trigger current | $V_D = 6\text{ V}$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 30 | mA |
| | | | $T_{VJ} = -40^{\circ}\text{C}$ | | 50 | mA |
| V_{GD} | gate non-trigger voltage | $V_D = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 150^{\circ}\text{C}$ | | 0.2 | V |
| I_{GD} | gate non-trigger current | | | | 1 | mA |
| I_L | latching current | $t_p = 10\text{ }\mu\text{s}$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 45 | mA |
| | | $I_G = 0.1\text{ A}; di_G/dt = 0.1\text{ A}/\mu\text{s}$ | | | | |
| I_H | holding current | $V_D = 6\text{ V}$ $R_{GK} = \infty$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 30 | mA |
| t_{gd} | gate controlled delay time | $V_D = \frac{1}{2} V_{DRM}$ | $T_{VJ} = 25^{\circ}\text{C}$ | | 2 | μs |
| | | $I_G = 0.1\text{ A}; di_G/dt = 0.1\text{ A}/\mu\text{s}$ | | | | |
| t_q | turn-off time | $V_R = 100\text{ V}; I_T = 5\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$ | | 150 | | μs |



| Package TO-263 (D2Pak-HV) | | | Ratings | | | |
|---------------------------|--|----------------------|---------|------|------|------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| I_{RMS} | RMS current | per terminal | | | 20 | A |
| T_{VJ} | virtual junction temperature | | -40 | | 150 | °C |
| T_{op} | operation temperature | | -40 | | 125 | °C |
| T_{stg} | storage temperature | | -40 | | 150 | °C |
| Weight | | | | 1.5 | | g |
| F_C | mounting force with clip | | 20 | | 60 | N |
| $d_{Spp/App}$ | creepage distance on surface / striking distance through air | terminal to terminal | 4.2 | | | mm |
| $d_{Spb/Apb}$ | | terminal to backside | 4.7 | | | mm |

Product Marking



Part description

- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 5 = Current Rating [A]
- E = Single Thyristor
- 1200 = Reverse Voltage [V]
- PZ = TO-263AB (D2Pak) (2HV)

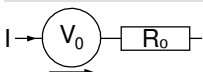
| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|-------------|-----------------|--------------------|---------------|----------|----------|
| Standard | CLA5E1200PZ-TRL | CLA5E1200PZ | Tape & Reel | 800 | 516482 |
| Alternative | CLA5E1200PZ-TUB | CLA5E1200PZ | Tube | 50 | 525276 |

| Similar Part | Package | Voltage class |
|--------------|-----------------|---------------|
| CLA5E1200UC | TO-252AA (DPak) | 1200 |

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150\text{ °C}$

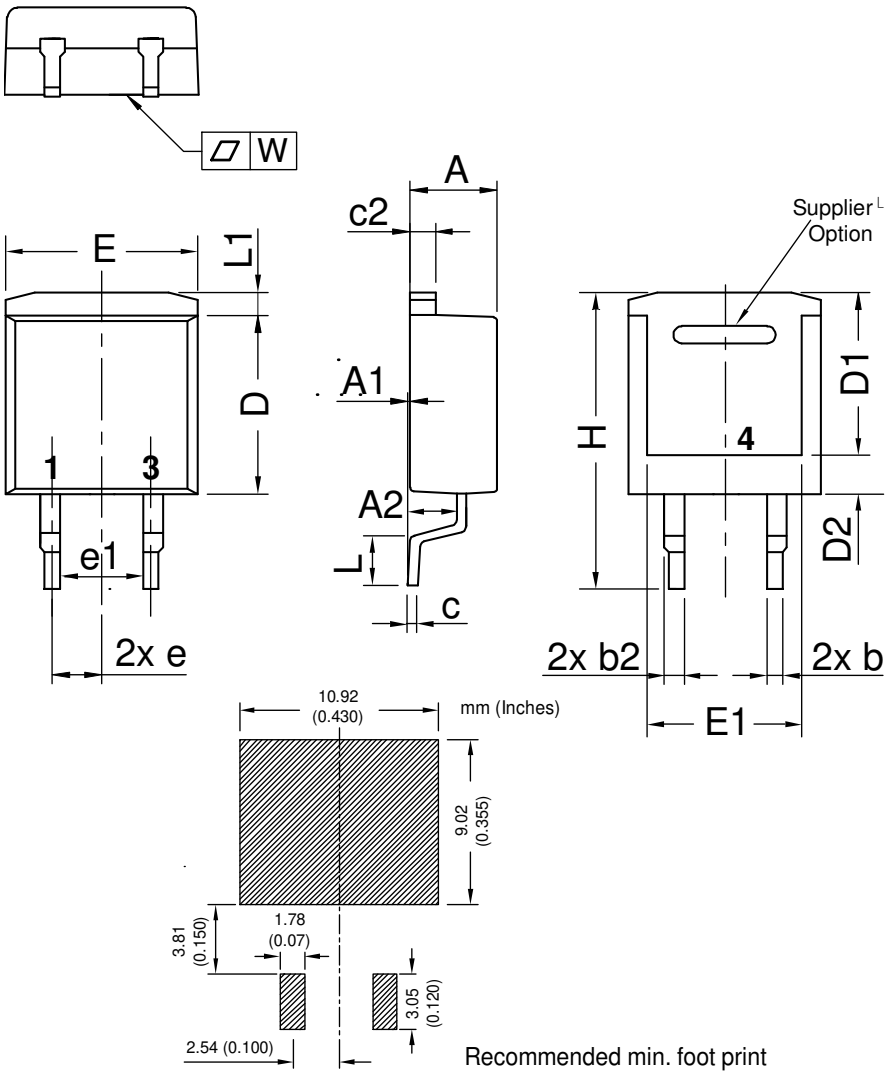


Thyristor

| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0.89 | V |
| $R_{0\ max}$ | slope resistance * | 82 | mΩ |



Outlines TO-263 (D2Pak-HV)



| Dim. | Millimeter | | Inches | |
|------|------------|-------|-------------|-------|
| | min | max | min | max |
| A | 4.06 | 4.83 | 0.160 | 0.190 |
| A1 | typ. 0.10 | | typ. 0.004 | |
| A2 | 2.41 | | 0.095 | |
| b | 0.51 | 0.99 | 0.020 | 0.039 |
| b2 | 1.14 | 1.40 | 0.045 | 0.055 |
| c | 0.40 | 0.74 | 0.016 | 0.029 |
| c2 | 1.14 | 1.40 | 0.045 | 0.055 |
| D | 8.38 | 9.40 | 0.330 | 0.370 |
| D1 | 8.00 | 8.89 | 0.315 | 0.350 |
| D2 | 2.3 | | 0.091 | |
| E | 9.65 | 10.41 | 0.380 | 0.410 |
| E1 | 6.22 | 8.50 | 0.245 | 0.335 |
| e | 2,54 BSC | | 0,100 BSC | |
| e1 | 4.28 | | 0.169 | |
| H | 14.61 | 15.88 | 0.575 | 0.625 |
| L | 1.78 | 2.79 | 0.070 | 0.110 |
| L1 | 1.02 | 1.68 | 0.040 | 0.066 |
| W | typ. 0.02 | 0.040 | typ. 0.0008 | 0.002 |

All dimensions conform with and/or within JEDEC standard.

